

HiPerFET™

Power MOSFETs

Q-Class

N-Channel Enhancement Mode
Avalanche Rated, Low Q_g , High dv/dt

Preliminary data sheet

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	300	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1\text{ M}\Omega$	300	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	66	A
I_{DM}	$T_C = 25^\circ\text{C}$, Note1	292	A
I_{AR}	$T_C = 25^\circ\text{C}$	73	A
E_{AR}	$T_C = 25^\circ\text{C}$	60	mJ
E_{AS}		2.5	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2\text{ }\Omega$	5	V/ns
P_D	$T_C = 25^\circ\text{C}$	400	W
T_J		-55 to +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 to +150	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS $t = 1\text{ min}$ $I_{ISOL} \leq 1\text{ mA}$ $t = 1\text{ s}$	2500 3000	V~ V~
M_d	Mounting torque Terminal connection torque	1.5/13 1.5/13	Nm/lb.in. Nm/lb.in.
Weight		19	g

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$	300		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4\text{ mA}$	2.0		4.0 V
I_{GSS}	$V_{GS} = \pm 20\text{ V}$, V_{DC} , $V_{DS} = 0$			$\pm 100\text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0\text{ V}$	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		100 μA 2 mA
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = I_T$ Note1			46 m Ω

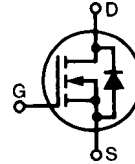
IXFE 73N30Q

$V_{DSS} = 300\text{ V}$

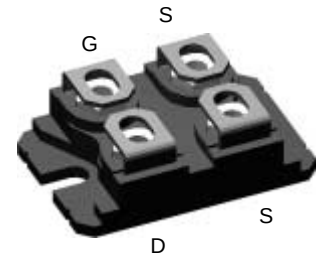
$I_{D25} = 66\text{ A}$

$R_{DS(on)} = 46\text{ m}\Omega$

$t_{rr} \leq 250\text{ ns}$



ISOPLUS227™ (IXFE)



G = Gate
S = Source

D = Drain

Either Source terminal at miniBLOC can be used as Main or Kelvin Source

Features

- Conforms to SOT-227B outline
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- Fast intrinsic Rectifier

Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- Temperature and lighting controls

Advantages

- Low cost
- Easy to mount
- Space savings
- High power density

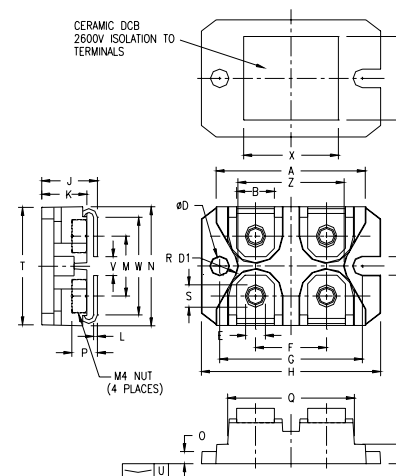
Symbol	Test Conditions	Characteristic Values ($T_j = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = I_T$, Note2	30	47	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		6400	pF
C_{oss}			1340	pF
C_{rss}			340	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = I_T$ $R_G = 1.0\ \Omega$ (External),		37	ns
t_r			36	ns
$t_{d(off)}$			82	ns
t_f			12	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = I_T$		190	nC
Q_{gs}			51	nC
Q_{gd}			78	nC
R_{thJC}			0.07	0.31 K/W
R_{thCK}				K/W

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values ($T_j = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$			73 A
I_{SM}	Repetitive; pulse width limited by T_{JM}			292 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.5 V
t_{rr}	$I_F = 25\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$		0.8	250 ns
Q_{RM}				μC
I_{RM}				A

- Notes: 1. Pulse width limited by T_{JM} .
 2. Pulse test, $t \leq 300\text{ ms}$, duty cycle $d \leq 2\%$.
 3. I_T Test current: $I_T = 36.5\text{ A}$

ISOPLUS-227 B



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.270	31.50	32.26
B	.310	.330	7.87	8.38
C	.155	.165	3.94	4.19
D	.155	.165	3.94	4.19
D1	.150	.157	3.81	3.98
E	.160	.168	4.06	4.27
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.489	1.505	37.80	38.23
J	.465	.481	11.81	12.22
K	.370	.380	9.40	9.65
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.100	.105	2.54	2.67
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.160	.170	4.06	4.32
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.001	.002	-0.03	0.05
V	.130	.160	3.30	4.06
W	.780	.830	19.81	21.08
X	.770	.810	19.56	20.57
Y	.680	.720	17.27	18.29
Z	.885	.892	22.48	22.66

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1
4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	